

TOSHIBA GTR MODULE SILICON N CHANNEL IGBT

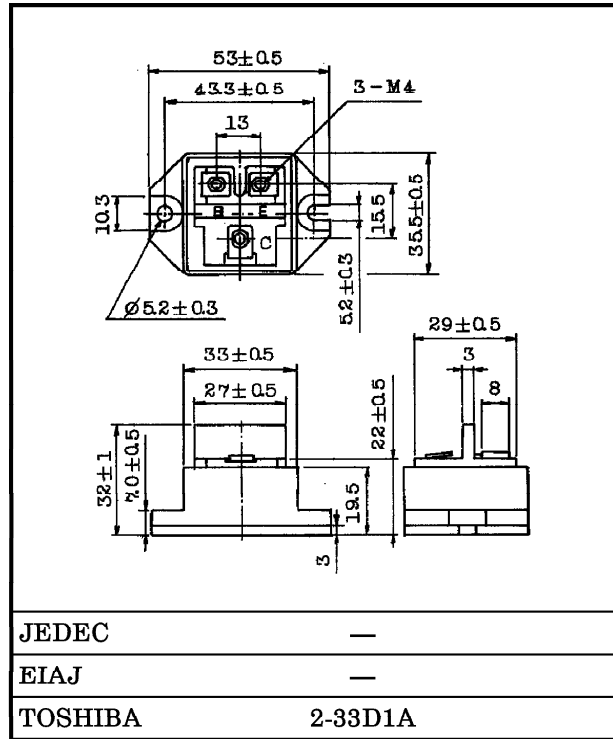
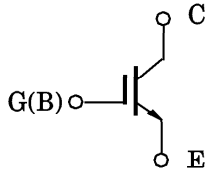
MG75Q1BS11

HIGH POWER SWITCHING APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

Unit in mm

- High Input Impedance
- High Speed : $t_f = 1.0 \mu s$ (Max.)
- Low Saturation Voltage: $V_{CE(sat)} = 2.7V$ (Max.)
- Enhancement-Mode
- The Electrodes are Isolated from Case.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	1200	V
Gate-Emitter Voltage	V_{GES}	±20	V
Collector Current	DC	I_C	A
	1ms	I_{CP}	
Collector Power Dissipation (Tc = 25°C)	P_C	300	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-40~125	°C
Isolation Voltage	V_{Isol}	2500 (AC 1 Minute)	V
Screw Torque (Terminal / Mounting)	—	2 / 3	N·m

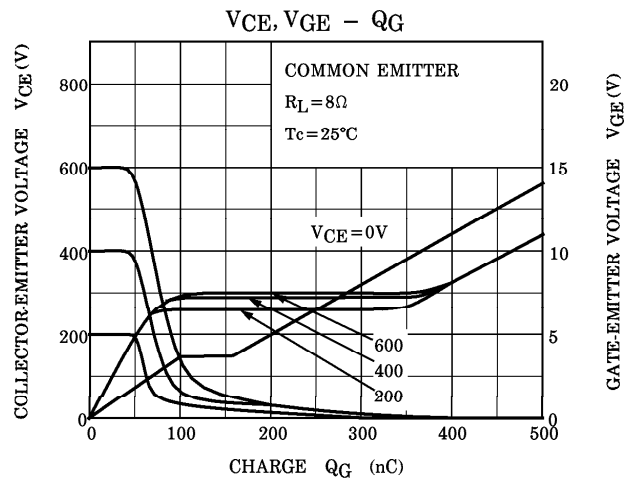
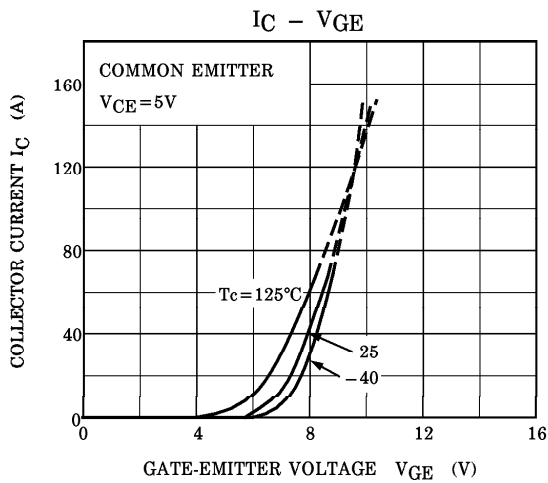
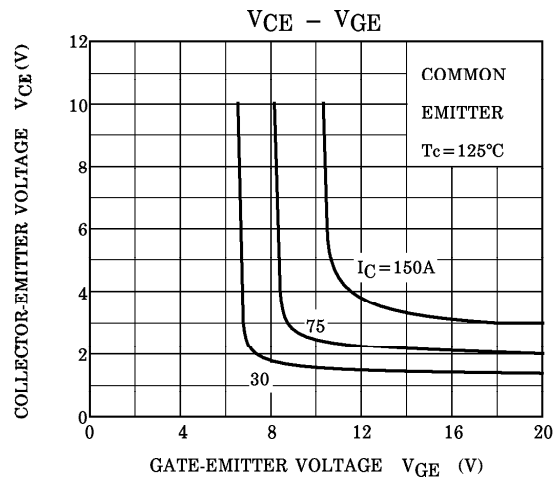
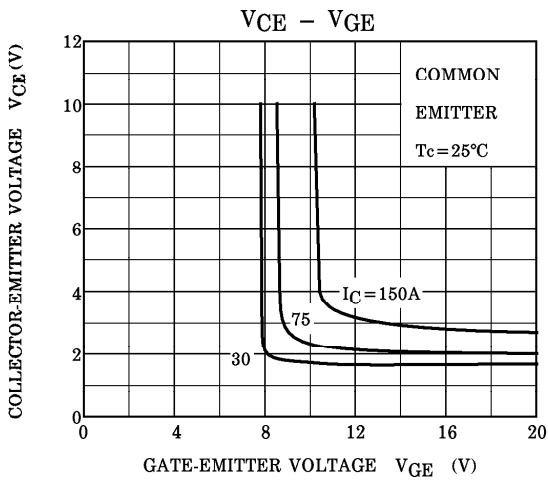
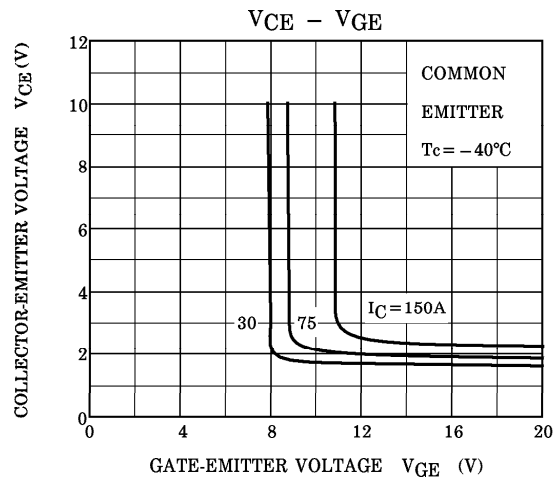
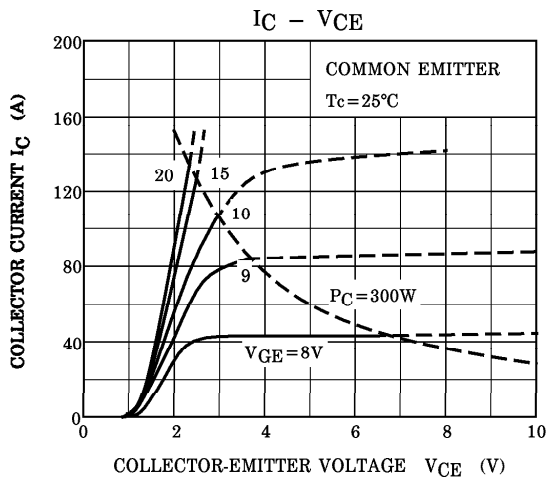
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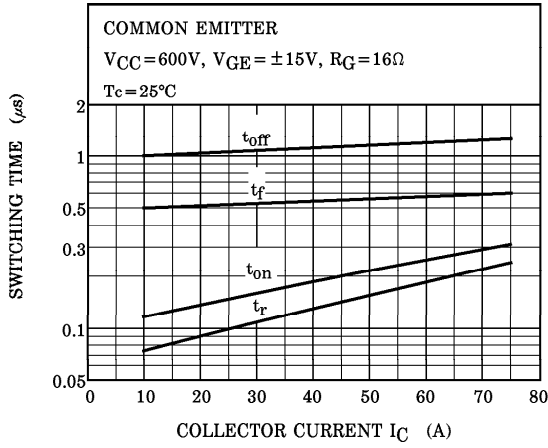
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA
Collector Cut-off Current		I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	—	—	1.0	mA
Collector-Emitter Voltage		V_{CES}	$I_C \leq 1mA, V_{GE} = 0$ Note 1	1200	—	—	V
Gate-Emitter Cut-off Voltage		$V_{GE} (OFF)$	$I_C = 75mA, V_{CE} = 5V$	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 75A, V_{GE} = 15V$	—	2.3	2.7	V
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0,$ $f = 1MHz$	—	10500	—	pF
Switching Time	Rise Time	t_r		—	0.3	0.6	μs
	Turn-on Time	t_{on}		—	0.4	0.8	
	Fall Time	t_f		—	0.6	1.0	
	Turn-off Time	t_{off}		—	1.2	1.6	
Thermal Resistance		$R_{th} (j-c)$	—	—	—	0.41	°C/W

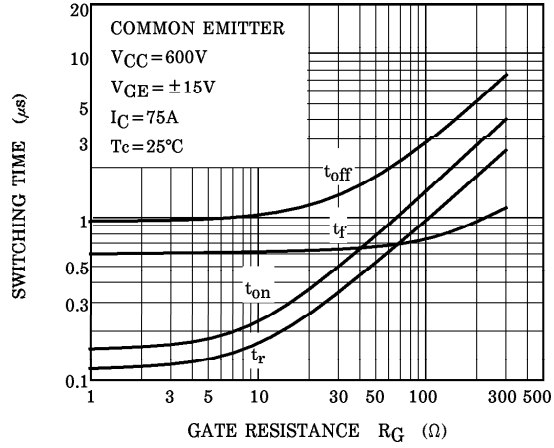
Note 1: Do not apply the over rating voltage.



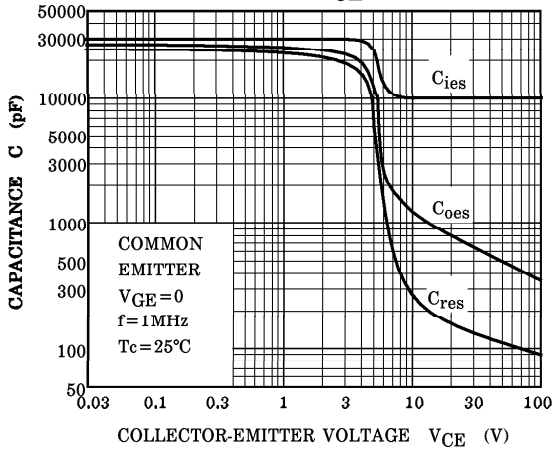
SWITCHING TIME - I_C



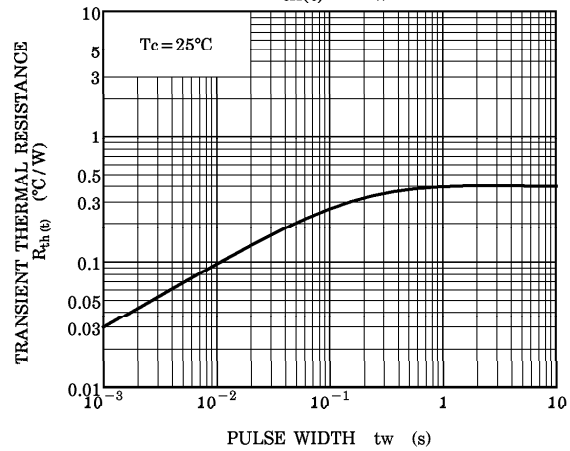
SWITCHING TIME - R_G



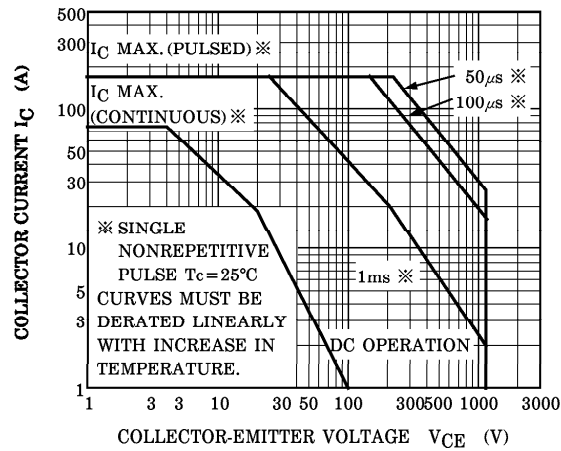
C - V_{CE}



$R_{th}(t) - t_w$



SAFE OPERATING AREA



REVERSE BIAS SOA

